PATENT ASSIGNMENT COVER SHEET

Electronic Version v1.1 Stylesheet Version v1.2 EPAS ID: PAT6751667

SUBMISSION TYPE:	NEW ASSIGNMENT
NATURE OF CONVEYANCE:	ASSIGNMENT

CONVEYING PARTY DATA

Name	Execution Date
GUANGTAO HAN	06/07/2021

RECEIVING PARTY DATA

Name:	JOULWATT TECHNOLOGY CO., LTD	
Street Address:	RM 901-23, 9TH FLOOR, BLD. 4, 298 ZHENHUA RD.	
Internal Address:	SANDUN TOWN XIHU DISTRICT	
City:	HANGZHOU	
State/Country:	CHINA	

PROPERTY NUMBERS Total: 1

Property Type	Number
Application Number:	17342489

CORRESPONDENCE DATA

Fax Number:

Correspondence will be sent to the e-mail address first; if that is unsuccessful, it will be sent using a fax number, if provided; if that is unsuccessful, it will be sent via US Mail.

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ATTORNEY DOCKET NUMBER:	21216CC
NAME OF SUBMITTER:	QING YE
SIGNATURE:	/Qing Ye/
DATE SIGNED:	06/09/2021

Total Attachments: 3

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PATENT 506704848 REEL: 056475 FRAME: 0606

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SEMICONDUCTOR STRUCTURE AND METHOD FOR MANUFACTURING THE
SAME

<u>ASSIGNMENT</u>

WHEREAS I/We, the below named inventor(s),
Guangtao HAN of Hangzhou, China

hereby sell and assign to Joulwatt Technology Co., Ltd., whose post office address is Room 901-23, 9th Floor, Building 4, West Port Development Center, NO. 298 ZHEN HUA Road, Sandun Town Xihu District, Hangzhou Zhejiang Province 310030, China, hereinafter referred to as "Company", its successors and assigns our entire respective rights, titles and interests in and to the invention and improvements invented and originated by us and for United States Patent currently entitled:

SEMICONDUCTOR STRUCTURE AND METHOD FOR MANUFACTURING THE SAME

Executed concurrently herewith,

and any and all applications for patent and patents therefrom in any and all countries, including all divisions, continuations, reexaminations and reissues thereof, and all rights of priority resulting from the filing of said United States application, and authorize and request any official whose duty it is to issue patents, to issue any patent on said inventions and improvements resulting therefrom to said Company, or its successors or assigns and agree that on request and without further consideration, but at the expense of said Company, we will communicate to said Company or its representatives or nominees any facts known to us respecting said inventions and improvements and testify in any legal proceeding, sign all lawful papers, execute all divisional, continuation, reexamination and reissue applications, make all rightful oaths and generally do everything possible to aid said Company, its successors, assigns, and nominees to obtain and enforce proper patent protection for said invention and its improvements in all countries.

AND We/I hereby authorize and request our/my agents, USPTO customer number 93229, whose address is 106 Oakland PI, Los Gatos, CA 95032, to insert hereon any

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identification necessary or desirable for recordation of this document, including the filing date and application number of said application when known.

AND We/I hereby covenant for ourselves/myself and our/my legal representatives, and agree with said Company, its successors and assigns, that We/I have granted no right or license to make, use, sell or offer to sell said improvements, to anyone except said Company, that prior to the execution of this assignment document, our/my right, title and interest in said improvements had not been otherwise encumbered, and that We/I have not and will not execute any instrument in conflict therewith:

AND We/I do hereby authorize and request the Director of the United States
Patent and Trademark Office to issue any and all letters patent which may be granted
upon said United States applications, or upon said improvements or any parts thereof
when granted, to said Company.

SEMICONDUCTOR STRUCTURE AND METHOD FOR MANUFACTURING THE SAME				
INVENTOR 1				
Signature: Guangtao HAN Guangtao HAN	Date: <u>06/07/2021</u>			
Witnessed by: Xinyan Wang Xinran WANG	Date: <u>06/07/2021</u>			
Witnessed by: Fei YE	Date: <u>06/07/2021</u>			